

# PATENT ABSTRACTS OF JAPAN

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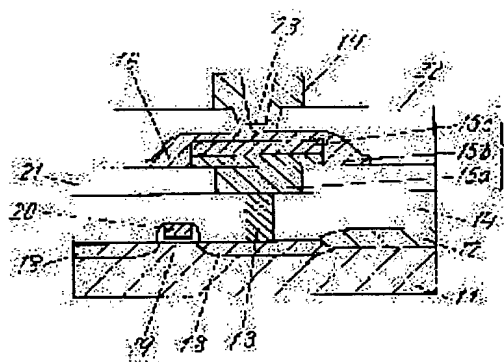
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## (54) FERRODIELECTRIC MEMORY DEVICE

### (57)Abstract:

PROBLEM TO BE SOLVED: To prevent hydrogen from infiltrating the capacitor part of a ferroelectric memory device and causing malfunctions due to deterioration of the capacitor by hydrogen.

SOLUTION: The ferroelectric memory device is constituted by forming on a silicon substrate 11 a device isolating oxide film 12, interlayer insulating film 14 having a contact plug 13, ferroelectric capacitor 15 which includes a lower electrode 15a and a capacitor insulating film 15b made of a ferroelectric material and an upper electrode 15c, conductive hydrogen barrier film 16, interlayer insulating film 22 having a contact hole 23, and wiring layer 17 formed in the contact hole 23. The conductive hydrogen barrier film 16 is formed of a TiAl alloy or TiAl nitride or a partially oxidized material of these materials.



## LEGAL STATUS

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